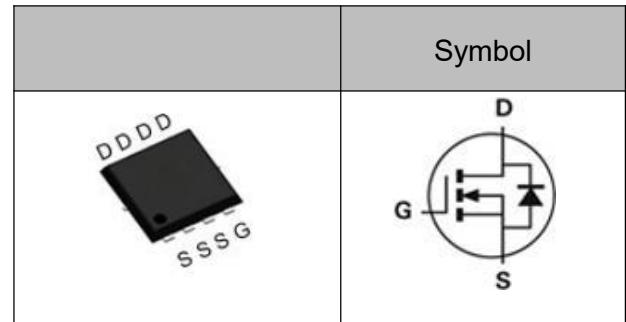


Features

- ◆ 120V, 132A, $R_{DS(ON)}(Typ.) = 6m\Omega @ V_{GS} = 10V$.
- ◆ Reliable and Rugged
- ◆ Fast Switching Speed
- ◆ Green Device Available
- ◆ 100% EAS Guaranteed

Application

- ◆ High Frequency Switching and Synchronous
- ◆ DC/DC Converter



PDFN5*6

Absolute Maximum Ratings $T_c = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Unit
V_{DS}	Drain-Source Voltage	120	V
V_{GS}	Gate-Source Voltage	± 20	
I_D	Drain Current-Continuous, $T_c = 25^\circ C$	132	A
	Drain Current-Continuous, $T_c = 100^\circ C$	83	
I_{DM}	Drain Current-Pulsed ^a	330	
E_{AS}	Avalanche Energy, Single pulse ^b	65	mJ
I_{AS}	Avalanche Current	36	A
P_D	Maximum Power Dissipation @ $T_c = 25^\circ C$	125	W
T_{STG}	Store Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case Max	-	1	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient Max ^c	-	48	$^\circ C/W$

Electrical Characteristics $T_J = 25^\circ C$ unless otherwise noted

Off Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	120	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 96V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Forward Gate Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA



■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	-	3.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ^d	$V_{GS} = 10V, I_D = 20A$	-	6	7.2	mΩ
		$V_{GS} = 4.5V, I_D = 10A$	-	8	10.4	
gfs	Forward Transconductance	$V_{DS} = 5V, I_D = 10A$	-	36	-	S

■ Dynamic Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{DS} = 60V,$ $V_{GS} = 0V,$ $f = 1.0MHz$	-	4849	-	pF
C_{oss}	Output Capacitance		-	458	-	
C_{rss}	Reverse Transfer Capacitance		-	32	-	

■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 60V, I_D = 1A,$ $R_G = 1\Omega, V_{GS} = 10V$	-	14.6	-	ns
t_r	Turn-On Rise Time		-	19.1	-	
$t_{d(off)}$	Turn-Off Delay Time		-	56.3	-	
t_f	Turn-Off Fall Time		-	103.7	-	
Qg	Total Gate Charge	$V_{DS} = 60V, I_D = 20A,$ $V_{GS} = 4.5V$	-	47	-	nC
Qg	Total Gate Charge	$V_{DS} = 60V, I_D = 20A,$ $V_{GS} = 10V$	-	94.7	-	
Qgs	Gate-Source Charge		-	19.7	-	
Qgd	Gate-Drain Charge		-	22.3	-	

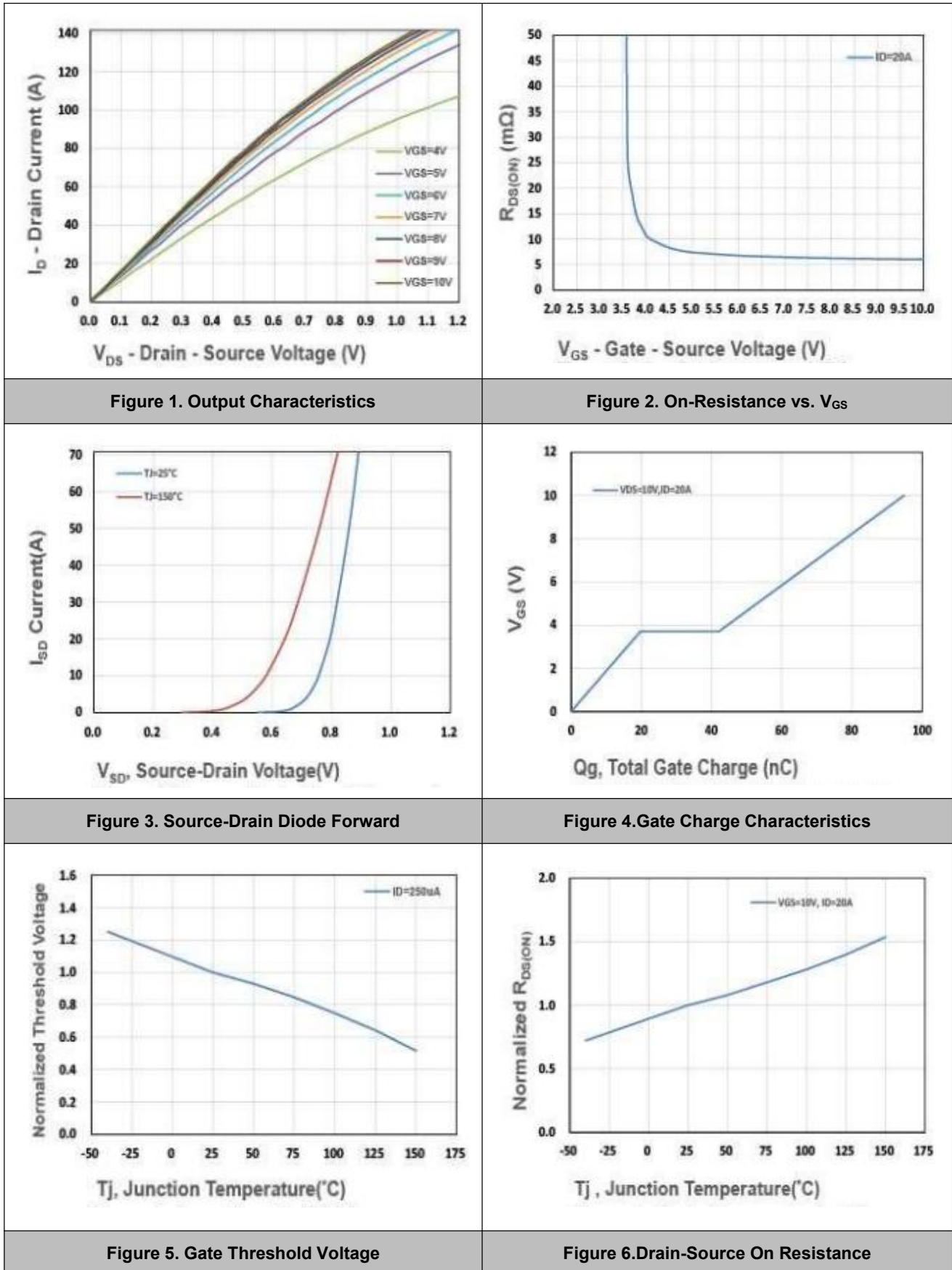
■ Drain-Source Diode Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
R_G	Gate Resistance	$V_{DS} = V_{GS} = 0V,$ Freq.=1MHz	-	0.6	-	Ω
I_S	Continuous Source Current	$V_G = V_D = 0V,$ Force Current	-	-	114	A
V_{SD}	Drain-Source Diode Forward Voltage ^d	$V_{GS} = 0V, I_{SD} = 10A$	-	0.75	1.1	V
t_{rr}	Reverse Recovery Time	$I_F = 10A, V_R = 60V$ $di/dt = 1A/us,$ $T_J = 25^\circ C$	-	73	-	ns
Q_{rr}	Reverse Recovery Charge		-	138	-	nC

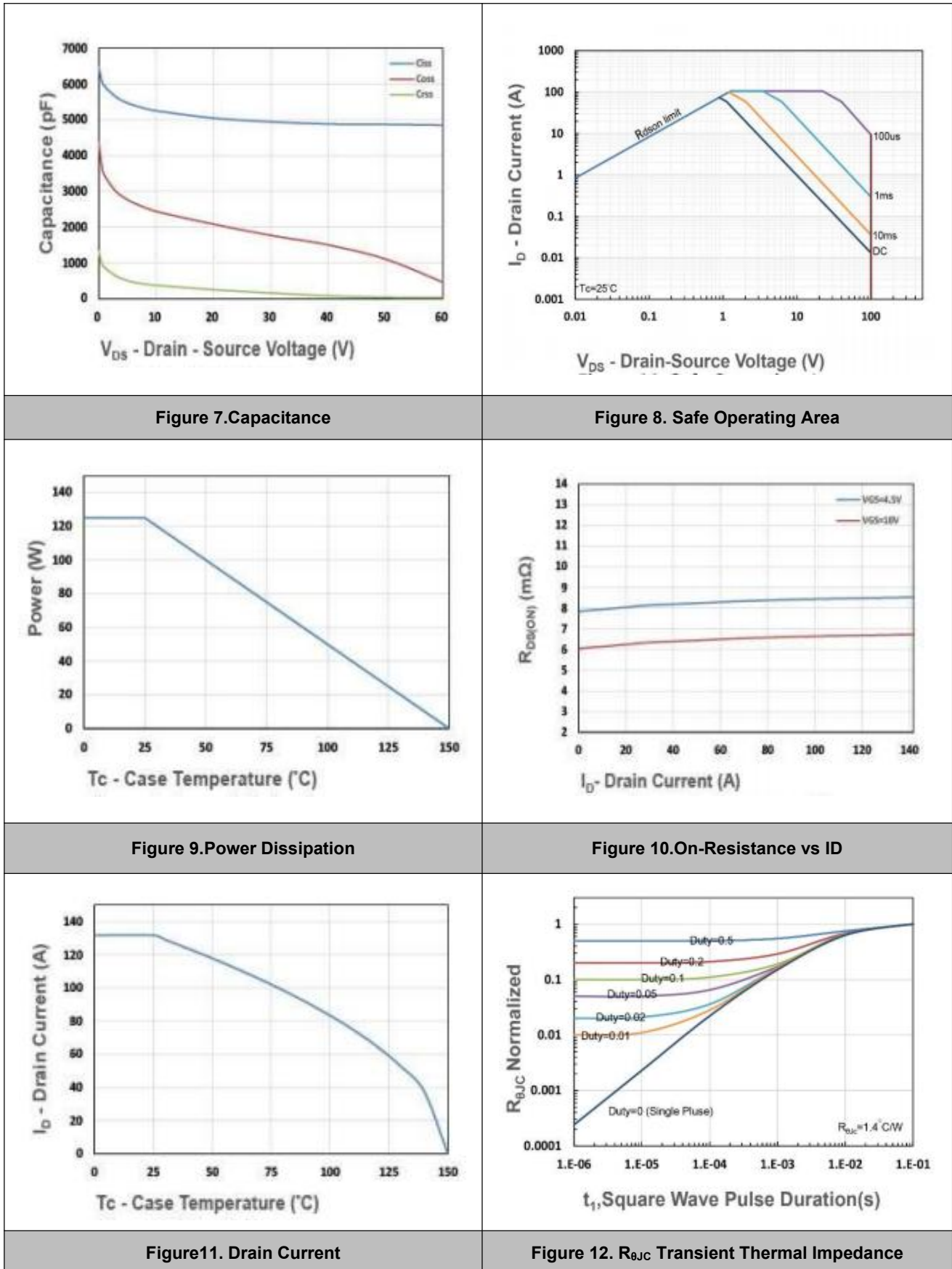
Notes:

- a: Max. current is limited by junction temperature.
- b: The EAS data shows Max. Rating. The test condition is $V_{DD} = 50V, V_{GS} = 10V, L = 0.1mH, I_{AS} = 23A$.
- c: Surface Mounted on 1in2 FR-4 board with 1oz.
- d: Pulse test (pulse width $\leq 300us$, duty cycle $\leq 2\%$).
- e: Guaranteed by design, not subject to production testing.

Typical Characteristics



■ Typical Characteristics



■ Package Information

PDFN5 × 6

Unit:mm

